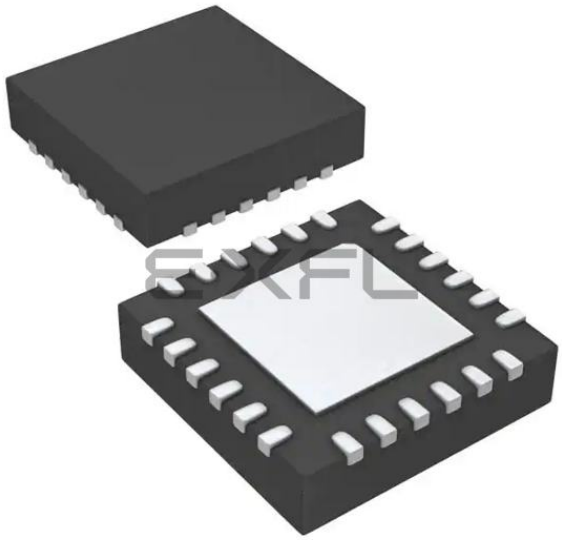

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	I²C, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, LVD, POR, PWM, WDT
Number of I/O	22
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 7x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	24-VFQFN Exposed Pad
Supplier Device Package	24-QFN (4x4)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mkl03z32vfk4

Ordering Information[1]

Part Number	Memory		Maximum number of I\O's
	Flash (KB)	SRAM (KB)	
MKL03Z8VFG4(R)	8	2	14
MKL03Z16VFG4(R)	16	2	14
MKL03Z32VFG4(R)	32	2	14
MKL03Z32CAF4R	32	2	18
MKL03Z8VFK4(R)	8	2	22
MKL03Z16VFK4(R)	16	2	22
MKL03Z32VFK4(R)	32	2	22

1. To confirm current availability of ordererable part numbers, go to http://www.freescale.com and perform a part number search.

Related Resources

Type	Description	Resource
Selector Guide	The Freescale Solution Advisor is a web-based tool that features interactive application wizards and a dynamic product selector.	Solution Advisor
Product Brief	The Product Brief contains concise overview/summary information to enable quick evaluation of a device for design suitability.	KL03PB[1]
Reference Manual	The Reference Manual contains a comprehensive description of the structure and function (operation) of a device.	KL03P24M48SF0RM[1]
Data Sheet	The Data Sheet includes electrical characteristics and signal connections.	KL03P24M48SF0[1]
Chip Errata	The chip mask set Errata provides additional or corrective information for a particular device mask set.	KL03Z_1N86K[1]
Package drawing	Package dimensions are provided in package drawings.	QFN 16-pin: 98ASA00525D[1] QFN 24-pin: 98ASA00602D[1] WLCSP 20-pin: 98ASA00676D[1]

1. To find the associated resource, go to http://www.freescale.com and perform a search using this term.

Figure 1 shows the functional modules in the chip.

Table of Contents

1.4 Voltage and current operating ratings

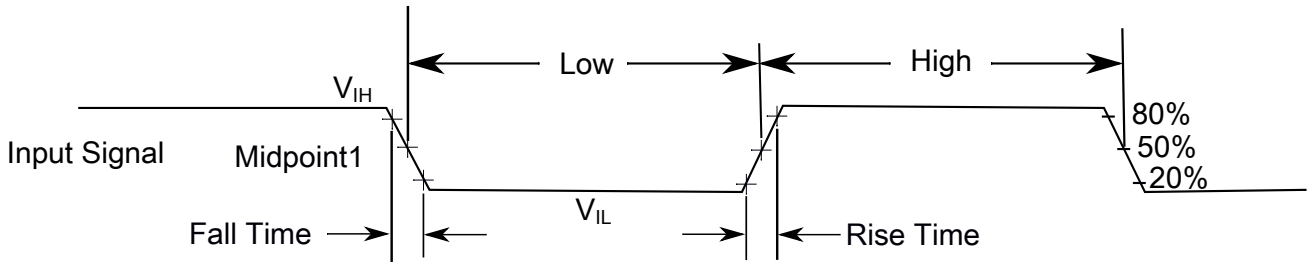
Table 4. Voltage and current operating ratings

Symbol	Description	Min.	Max.	Unit
V_{DD}	Digital supply voltage	–0.3	3.8	V
I_{DD}	Digital supply current	—	120	mA
V_{IO}	IO pin input voltage	–0.3	V_{DD} + 0.3	V
I_D	Instantaneous maximum current single pin limit (applies to all port pins)	–25	25	mA
V_{DDA}	Analog supply voltage	V_{DD} – 0.3	V_{DD} + 0.3	V

2 General

2.1 AC electrical characteristics

Unless otherwise specified, propagation delays are measured from the 50% to the 50% point, and rise and fall times are measured at the 20% and 80% points, as shown in the following figure.



The midpoint is V_{IL} + (V_{IH} - V_{IL}) / 2

Figure 2. Input signal measurement reference

All digital I/O switching characteristics, unless otherwise specified, assume the output pins have the following characteristics.

- C_L=30 pF loads
- Slew rate disabled
- Normal drive strength

2.2 Nonswitching electrical specifications

Table 6. V_{DD} supply LVD and POR operating requirements (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{LVW3H}	• Level 3 falling (LVWV = 10)	2.82	2.90	2.98	V	
V_{LVW4H}	• Level 4 falling (LVWV = 11)	2.92	3.00	3.08	V	
V_{HYSH}	Low-voltage inhibit reset/recover hysteresis — high range	—	±60	—	mV	—
V_{LVDL}	Falling low-voltage detect threshold — low range (LVDV=00)	1.54	1.60	1.66	V	—
	Low-voltage warning thresholds — low range					1
V_{LVW1L}	• Level 1 falling (LVWV = 00)	1.74	1.80	1.86	V	
V_{LVW2L}	• Level 2 falling (LVWV = 01)	1.84	1.90	1.96	V	
V_{LVW3L}	• Level 3 falling (LVWV = 10)	1.94	2.00	2.06	V	
V_{LVW4L}	• Level 4 falling (LVWV = 11)	2.04	2.10	2.16	V	
V_{HYSL}	Low-voltage inhibit reset/recover hysteresis — low range	—	±40	—	mV	—
V_{BG}	Bandgap voltage reference	0.97	1.00	1.03	V	—
t_{LPO}	Internal low power oscillator period — factory trimmed	900	1000	1100	µs	—

1. Rising thresholds are falling threshold + hysteresis voltage

2.2.3 Voltage and current operating behaviors

Table 7. Voltage and current operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
V_{OH}	Output high voltage — Normal drive pad (except $\overline{\text{RESET}}$)				1, 2
	• 2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OH} = –5 mA	V_{DD} – 0.5	—	V	
	• 1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OH} = –2.5 mA	V_{DD} – 0.5	—	V	
V_{OH}	Output high voltage — High drive pad (except $\overline{\text{RESET}}$)				1, 2
	• 2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OH} = –20 mA	V_{DD} – 0.5	—	V	
	• 1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OH} = –10 mA	V_{DD} – 0.5	—	V	
I_{OHT}	Output high current total for all ports	—	100	mA	—
V_{OL}	Output low voltage — Normal drive pad				1
	• 2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OL} = 5 mA	—	0.5	V	
	• 1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OL} = 2.5 mA	—	0.5	V	
V_{OL}	Output low voltage — High drive pad				1

Table continues on the next page...

Table 9. KL03 QFN packages power consumption operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.[1]	Unit	Notes
I_{DD_VLPRCO}	Very-low-power run While(1) loop in SRAM in compute operation mode:—2 MHz LIRC mode, 2 MHz core / 0.5 MHz flash, V_{DD} = 3.0 V • at 25 °C	—	82	123	µA	—
I_{DD_VLPR}	Very-low-power run mode current— 2 MHz LIRC mode, While(1) loop in flash all peripheral clock disable, 2 MHz core / 0.5 MHz flash, V_{DD} = 3.0 V • at 25 °C	—	503	754	µA	—
I_{DD_VLPR}	Very-low-power run mode current— 2 MHz LIRC mode, While(1) loop in flash all peripheral clock disable, 125 kHz core / 31.25 kHz flash, V_{DD} = 3.0 V • at 25 °C	—	60	90	µA	—
I_{DD_VLPR}	Very-low-power run mode current— 2 MHz LIRC mode, While(1) loop in flash all peripheral clock enable, 2 MHz core / 0.5 MHz flash, V_{DD} = 3.0 V • at 25 °C	—	516	774	µA	—
I_{DD_VLPR}	Very-low-power run mode current— 8 MHz LIRC mode, While(1) loop in SRAM in all peripheral clock disable, 4 MHz core / 1 MHz flash, V_{DD} = 3.0 V • at 25 °C	—	209	350	µA	—
I_{DD_VLPR}	Very-low-power run mode current— 8 MHz LIRC mode, While(1) loop in SRAM all peripheral clock enable, 4 MHz core / 1 MHz flash, V_{DD} = 3.0 V • at 25 °C	—	229	370	µA	—
I_{DD_VLPR}	Very-low-power run mode current—2 MHz LIRC mode, While(1) loop in SRAM in all peripheral clock disable, 2 MHz core / 0.5 MHz flash, V_{DD} = 3.0 V • at 25 °C	—	93	140	µA	—
I_{DD_VLPR}	Very-low-power run mode current—2 MHz LIRC mode, While(1) loop in SRAM all peripheral clock disable, 125 kHz core / 31.25 kHz flash, V_{DD} = 3.0 V • at 25 °C	—	31	81	µA	—
I_{DD_VLPR}	Very-low-power run mode current—2 MHz LIRC mode, While(1) loop in SRAM all peripheral clock enable, 2 MHz core / 0.5 MHz flash, V_{DD} = 3.0 V • at 25 °C	—	103	154	µA	—
I_{DD_WAIT}	Wait mode current—core disabled, 48 MHz system/24 MHz bus, flash disabled (flash doze enabled), all peripheral clocks disabled, MCG_Lite under HIRC mode, V_{DD} = 3.0 V	—	1.4	1.94	mA	—

Table continues on the next page...

Table 9. KL03 QFN packages power consumption operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.[1]	Unit	Notes
I_{DD_WAIT}	Wait mode current—core disabled, 24 MHz system/12 MHz bus, flash disabled (flash doze enabled), all peripheral clocks disabled, MCG_Lite under HIRC mode, V_{DD} = 3.0 V	—	1.02	1.24	mA	—
I_{DD_VLPW}	Very-low-power run wait current, core disabled, 4 MHz system/ 1 MHz bus and flash, all peripheral clocks disabled, V_{DD} = 3.0 V	—	121	181	µA	—
I_{DD_VLPW}	Very-low-power run wait current, core disabled, 2 MHz system/ 0.5 MHz bus and flash, all peripheral clocks disabled, V_{DD} = 3.0 V	—	59	97	µA	—
I_{DD_VLPW}	Very-low-power run wait current, core disabled, 125 kHz system/ 31.25 kHz bus and flash, all peripheral clocks disabled, V_{DD} = 3.0 V	—	28	42	µA	—
I_{DD_PSTOP2}	Partial Stop 2, core and system clock disabled, 12 MHz bus and flash, V_{DD} = 3.0 V	—	1.53	2.03	mA	—
I_{DD_PSTOP2}	Partial Stop 2, core and system clock disabled, flash doze enabled, 12 MHz bus, V_{DD} = 3.0 V	—	0.881	1.18	mA	—
I_{DD_STOP}	Stop mode current at 3.0 V • at 25 °C and below • at 50 °C • at 85 °C • at 105 °C	— — — —	158 164 187 219	175.7 179.48 199.54 236.43	µA	—
I_{DD_VLPS}	Very-low-power stop mode current at 3.0 V • at 25 °C and below • at 50 °C • at 85 °C • at 105 °C	— — — —	2.2 3.9 13.9 28.4	2.71 6.63 18.25 36.59	µA	—
I_{DD_VLPS}	Very-low-power stop mode current at 1.8 V • at 25 °C and below • at 50 °C • at 85 °C • at 105 °C	— — — —	2.2 3.8 13.2 27.8	2.674 6.44 17.37 35.54	µA	—
I_{DD_VLLS3}	Very-low-leakage stop mode 3 current, all peripheral disable, at 3.0 V • at 25 °C and below • at 50 °C • at 85 °C • at 105 °C	— — — —	1.08 1.4 3.45 7.02	1.17 1.52 3.96 8.19	µA	—

Table continues on the next page...

Table 10. KL03 WLCSP package power consumption operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.[1]	Unit	Notes
I_{DD_VLPRCO}	Very-low-power run While(1) loop in flash in compute operation mode— 2 MHz LIRC mode, 2 MHz core/0.5 MHz flash, V_{DD} = 3.0 V • at 25 °C	—	500	750	µA	—
I_{DD_VLPRCO}	Very-low-power-run While(1) loop in SRAM in compute operation mode— 8 MHz LIRC mode, 4 MHz core / 1 MHz flash, V_{DD} = 3.0 V • at 25 °C	—	188	217	µA	—
I_{DD_VLPRCO}	Very-low-power run While(1) loop in SRAM in compute operation mode:—2 MHz LIRC mode, 2 MHz core / 0.5 MHz flash, V_{DD} = 3.0 V • at 25 °C	—	82	123	µA	—
I_{DD_VLPR}	Very-low-power run mode current— 2 MHz LIRC mode, While(1) loop in flash all peripheral clock disable, 2 MHz core / 0.5 MHz flash, V_{DD} = 3.0 V • at 25 °C	—	503	754	µA	—
I_{DD_VLPR}	Very-low-power run mode current— 2 MHz LIRC mode, While(1) loop in flash all peripheral clock disable, 125 kHz core / 31.25 kHz flash, V_{DD} = 3.0 V • at 25 °C	—	60	90	µA	—
I_{DD_VLPR}	Very-low-power run mode current— 2 MHz LIRC mode, While(1) loop in flash all peripheral clock enable, 2 MHz core / 0.5 MHz flash, V_{DD} = 3.0 V • at 25 °C	—	516	774	µA	—
I_{DD_VLPR}	Very-low-power run mode current— 8 MHz LIRC mode, While(1) loop in SRAM in all peripheral clock disable, 4 MHz core / 1 MHz flash, V_{DD} = 3.0 V • at 25 °C	—	209	350	µA	—
I_{DD_VLPR}	Very-low-power run mode current— 8 MHz LIRC mode, While(1) loop in SRAM all peripheral clock enable, 4 MHz core / 1 MHz flash, V_{DD} = 3.0 V • at 25 °C	—	229	370	µA	—
I_{DD_VLPR}	Very-low-power run mode current—2 MHz LIRC mode, While(1) loop in SRAM in all peripheral clock disable, 2 MHz core / 0.5 MHz flash, V_{DD} = 3.0 V • at 25 °C	—	93	140	µA	—
I_{DD_VLPR}	Very-low-power run mode current—2 MHz LIRC mode, While(1) loop in SRAM all peripheral clock disable, 125 kHz core / 31.25 kHz flash, V_{DD} = 3.0 V • at 25 °C	—	31	81	µA	—
I_{DD_VLPR}	Very-low-power run mode current—2 MHz LIRC mode, While(1) loop in SRAM all					—

Table continues on the next page...

1. The maximum values represent characterized results equivalent to the mean plus three times the standard deviation (mean + 3 sigma).
2. The analog supply current is the sum of the active or disabled current for each of the analog modules on the device. See each module's specification for its supply current.
3. MCG_Lite configured for HIRC mode. CoreMark benchmark compiled using IAR 7.10 with optimization level high, optimized for balanced.
4. No brownout

Table 11. Low power mode peripheral adders — typical value

Symbol	Description	Temperature (°C)						Unit
		-40	25	50	70	85	105[1]	
$I_{LIRC8MHz}$	8 MHz internal reference clock (LIRC) adder. Measured by entering STOP or VLPS mode with 8 MHz LIRC enabled, MCG_SC[FCRDIV]=000b, MCG_MC[LIRC_DIV2]=000b.	68	68	68	68	68	68	µA
$I_{LIRC2MHz}$	2 MHz internal reference clock (LIRC) adder. Measured by entering STOP mode with the 2 MHz LIRC enabled, MCG_SC[FCRDIV]=000b, MCG_MC[LIRC_DIV2]=000b.	27	27	27	27	27	27	µA
$I_{EREFSTEN32KHz}$	External 32 kHz crystal clock adder by means of the OSC0_CR[EREFSTEN and EREFSTEN] bits. Measured by entering all modes with the crystal enabled. • VLLS1 • VLLS3 • VLPS • STOP	 340 340 340 340	 410 410 420 420	 460 460 480 480	 470 490 570 570	 480 530 610 610	 600 600 850 850	nA
I_{LPTMR}	LPTMR peripheral adder measured by placing the device in VLLS1 mode with LPTMR enabled using LPO.	30	30	30	85	100	200	nA
I_{CMP}	CMP peripheral adder measured by placing the device in VLLS1 mode with CMP enabled using the 6-bit DAC and a single external input for compare. Includes 6-bit DAC power consumption.	15	15	15	15	15	15	µA
I_{RTC}	RTC peripheral adder measured by placing the device in VLLS1 mode with external 32 kHz crystal enabled by means of the RTC_CR[OSCE] bit and the RTC ALARM set for 1 minute. Includes ERCLK32K (32 kHz external crystal) power consumption.	340	440	440	480	520	620	nA
I_{UART}	UART peripheral adder measured by placing the device in STOP or VLPS mode with selected clock source waiting for RX data at 115200 baud rate.							

Table continues on the next page...

Table 11. Low power mode peripheral adders — typical value (continued)

Symbol	Description	Temperature (°C)						Unit
		-40	25	50	70	85	105[1]	
	Includes selected clock source power consumption. • LIRC8M (8 MHz internal reference clock) • LIRC2M (2 MHz internal reference clock)	85 28	85 28	85 28	85 28	85 28	85 28	µA
I_{TPM}	TPM peripheral adder measured by placing the device in STOP or VLPS mode with selected clock source configured for output compare generating 100 Hz clock signal. No load is placed on the I/O generating the clock signal. Includes selected clock source and I/O switching currents. • LIRC8M (8 MHz internal reference clock) • LIRC2M (2 MHz internal reference clock)	93 35	93 35	93 35	93 35	93 35	93 35	µA
I_{BG}	Bandgap adder when BGEN bit is set and device is placed in VLPx or VLLSx mode.	45	45	45	45	45	45	µA
I_{ADC}	ADC peripheral adder combining the measured values at V_{DD} and V_{DDA} by placing the device in STOP or VLPS mode. ADC is configured for low power mode using the internal clock and continuous conversions.	340	340	340	340	340	340	µA

1. For QFN packages only.

2.2.5.1 Diagram: Typical IDD_RUN operating behavior

The following data was measured under these conditions:

- MCG-Lite in HIRC for run mode, and LIRC for VLPR mode
- No GPIOs toggled
- Code execution from flash
- For the ALLOFF curve, all peripheral clocks are disabled except FTFA

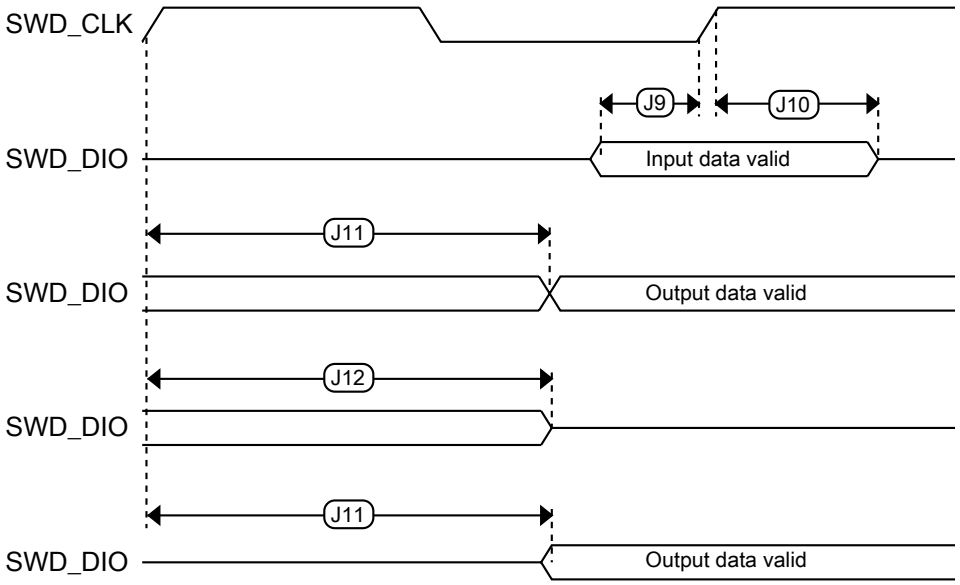


Figure 7. Serial wire data timing

3.2 System modules

There are no specifications necessary for the device's system modules.

3.3 Clock modules

3.3.1 MCG-Lite specifications

Table 20. HIRC48M specification

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{DD}	Supply voltage	1.71	—	3.6	V	—
I_{DD48M}	Supply current	—	400	500	µA	—
f_{irc48m}	Internal reference frequency	—	48	—	MHz	—
$\Delta f_{irc48m\_ol\_lv}$	total deviation of IRC48M frequency at low voltage (VDD=1.71V-1.89V) over temperature	—	± 0.5	±1.5	$\%f_{irc48m}$	—

Table continues on the next page...

Table 20. HIRC48M specification (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$\Delta f_{irc48m\_ol\_hv}$	total deviation of IRC48M frequency at high voltage (VDD=1.89V-3.6V) over temperature	—	± 0.5	±1.0	$\%f_{irc48m}$	—
J_{cyc_irc48m}	Period Jitter (RMS)	—	35	150	ps	—
$t_{irc48mst}$	Startup time	—	2	3	µs	1

1. IRC48M startup time is defined as the time between clock enablement and clock availability for system use. Enable the clock by setting MCG_MC[HIRCEN] = 1. See reference manual for details.

Table 21. LIRC8M/2M specification

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{DD}	Supply voltage	1.08	—	1.47	V	—
T	Temperature range	-40	—	125	°C	—
I_{DD_2M}	Supply current in 2 MHz mode	—	14	17	µA	—
I_{DD_8M}	Supply current in 8 MHz mode	—	30	35	µA	—
f_{IRC_2M}	Output frequency	—	2	—	MHz	—
f_{IRC_8M}	Output frequency	—	8	—	MHz	—
$f_{IRC\_T\_2M}$	Output frequency range (trimmed)	—	—	±3	$\%f_{IRC}$	V_{DD}≥1.89 V
$f_{IRC\_T\_8M}$	Output frequency range (trimmed)	—	—	±3	$\%f_{IRC}$	V_{DD}≥1.89 V
T_{su_2M}	Startup time	—	—	12.5	µs	—
T_{su_8M}	Startup time	—	—	12.5	µs	—

3.3.2 Oscillator electrical specifications

3.3.2.1 Oscillator DC electrical specifications

Table 22. Oscillator DC electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{DD}	Supply voltage	1.71	—	3.6	V	—
I_{DDOSC}	Supply current — low-power mode • 32 kHz	—	500	—	nA	1
C_x	EXTAL load capacitance	—	—	—		2, 3
C_y	XTAL load capacitance	—	—	—		2, 3
R_F	Feedback resistor — low-frequency, low-power mode	—	—	—	MΩ	2, 4
R_S	Series resistor — low-frequency, low-power mode	—	—	—	kΩ	—

Table continues on the next page...

Table 22. Oscillator DC electrical specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{pp}[5]	Peak-to-peak amplitude of oscillation (oscillator mode) — low-frequency, low-power mode	—	0.6	—	V	—

1. V_{DD}=3.3 V, Temperature =25 °C
2. See crystal or resonator manufacturer's recommendation
3. C_x,C_y can be provided by using either the integrated capacitors or by using external components.
4. When low power mode is selected, R_F is integrated and must not be attached externally.
5. The EXTAL and XTAL pins should only be connected to required oscillator components and must not be connected to any other devices.

3.3.2.2 Oscillator frequency specifications

Table 23. Oscillator frequency specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
f_{osc_lo}	Oscillator crystal or resonator frequency — low frequency mode	32	—	40	kHz	—
t_{dc_extal}	Input clock duty cycle (external clock mode)	40	50	60	%	—
t_{cst}	Crystal startup time — 32 kHz low-frequency, low-power mode	—	750	—	ms	1, 2

1. Proper PC board layout procedures must be followed to achieve specifications.
2. Crystal startup time is defined as the time between the oscillator being enabled and the OSCINIT bit in the MCG_S register being set.

3.4 Memories and memory interfaces

3.4.1 Flash electrical specifications

This section describes the electrical characteristics of the flash memory module.

3.4.1.1 Flash timing specifications — program and erase

The following specifications represent the amount of time the internal charge pumps are active and do not include command overhead.

Table 24. NVM program/erase timing specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
t_{hvpgm4}	Longword Program high-voltage time	—	7.5	18	µs	—
$t_{hversscr}$	Sector Erase high-voltage time	—	13	113	ms	1
$t_{hversall}$	Erase All high-voltage time	—	52	452	ms	1

1. Maximum time based on expectations at cycling end-of-life.

3.4.1.2 Flash timing specifications — commands

Table 25. Flash command timing specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$t_{rd1sec1k}$	Read 1s Section execution time (flash sector)	—	—	60	µs	1
t_{pgmchk}	Program Check execution time	—	—	45	µs	1
t_{rdrsrc}	Read Resource execution time	—	—	30	µs	1
t_{pgm4}	Program Longword execution time	—	65	145	µs	—
t_{ersscr}	Erase Flash Sector execution time	—	14	114	ms	2
t_{rd1all}	Read 1s All Blocks execution time	—	—	0.5	ms	—
t_{rdonce}	Read Once execution time	—	—	25	µs	1
$t_{pgmonce}$	Program Once execution time	—	65	—	µs	—
t_{ersall}	Erase All Blocks execution time	—	61	500	ms	2
t_{vfykey}	Verify Backdoor Access Key execution time	—	—	30	µs	1

1. Assumes 25 MHz flash clock frequency.
2. Maximum times for erase parameters based on expectations at cycling end-of-life.

3.4.1.3 Flash high voltage current behaviors

Table 26. Flash high voltage current behaviors

Symbol	Description	Min.	Typ.	Max.	Unit
I_{DD_PGM}	Average current adder during high voltage flash programming operation	—	2.5	6.0	mA
I_{DD_ERS}	Average current adder during high voltage flash erase operation	—	1.5	4.0	mA

3.4.1.4 Reliability specifications

Table 27. NVM reliability specifications

Symbol	Description	Min.	Typ.[1]	Max.	Unit	Notes
Program Flash						
$t_{nvmretp10k}$	Data retention after up to 10 K cycles	5	50	—	years	—
$t_{nvmretp1k}$	Data retention after up to 1 K cycles	20	100	—	years	—
$n_{nvmcycp}$	Cycling endurance	10 K	50 K	—	cycles	2

1. Typical data retention values are based on measured response accelerated at high temperature and derated to a constant 25 °C use profile. Engineering Bulletin EB618 does not apply to this technology. Typical endurance defined in Engineering Bulletin EB619.
2. Cycling endurance represents number of program/erase cycles at -40 °C ≤ T_j ≤ 125 °C.

Table 29. 12-bit ADC characteristics (V_{REFH} = V_{DDA}, V_{REFL} = V_{SSA}) (continued)

Symbol	Description	Conditions[1].	Min.	Typ.[2]	Max.	Unit	Notes
DNL	Differential non-linearity	• 12-bit modes	—	±0.9	–1.1 to +1.9	LSB[4]	5
		• <12-bit modes	—	±0.4	–0.3 to 0.5		
INL	Integral non-linearity	• 12-bit modes	—	±1.5	–2.7 to +1.9	LSB[4]	5
		• <12-bit modes	—	±0.5	–0.7 to +0.5		
E_{FS}	Full-scale error	• 12-bit modes	—	5	—	LSB[4]	V_{ADIN} = V_{DDA}[5]
		• <12-bit modes	—	2	3		
E_Q	Quantization error	• 12-bit modes	—	—	±0.5	LSB[4]	
E_{IL}	Input leakage error		$I_{In} \times R_{AS}$			mV	I_{In} = leakage current (refer to the MCU's voltage and current operating ratings)
	Temp sensor slope	Across the full temperature range of the device	1.55	1.62	1.69	mV/°C	6
V_{TEMP25}	Temp sensor voltage	25 °C	706	716	726	mV	6

1. All accuracy numbers assume the ADC is calibrated with V_{REFH} = V_{DDA}
2. Typical values assume V_{DDA} = 3.0 V, Temp = 25 °C, f_{ADCK} = 2.0 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.
3. The ADC supply current depends on the ADC conversion clock speed, conversion rate and ADC_CFG1[ADLPC] (low power). For lowest power operation, ADC_CFG1[ADLPC] must be set, the ADC_CFG2[ADHSC] bit must be clear with 1 MHz ADC conversion clock speed.
4. 1 LSB = (V_{REFH} - V_{REFL})/2^N
5. ADC conversion clock < 16 MHz, Max hardware averaging (AVGE = %1, AVGS = %11)
6. ADC conversion clock < 3 MHz

Table 30. 12-bit ADC characteristics (V_{REFH} = V_{REFO}, V_{REFL} = V_{SSA})

Symbol	Description	Conditions[1].	Min.	Typ.[2]	Max.	Unit	Notes
I_{DDA_ADC}	Supply current		0.215	—	1.7	mA	3
f_{ADACK}	ADC asynchronous clock source	• ADLPC = 1, ADHSC = 0	1.2	2.4	3.9	MHz	t_{ADACK} = $1/f_{ADACK}$
		• ADLPC = 1, ADHSC = 1	2.4	4.0	6.1	MHz	
		• ADLPC = 0, ADHSC = 0	3.0	5.2	7.3	MHz	
		• ADLPC = 0, ADHSC = 1	4.4	6.2	9.5	MHz	

Table continues on the next page...

Table 31. Comparator and 6-bit DAC electrical specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit
I_{DAC6b}	6-bit DAC current adder (enabled)	—	7	—	µA
INL	6-bit DAC integral non-linearity	–0.5	—	0.5	LSB[3]
DNL	6-bit DAC differential non-linearity	–0.3	—	0.3	LSB

1. Typical hysteresis is measured with input voltage range limited to 0.6 to V_{DD}–0.6 V.
2. Comparator initialization delay is defined as the time between software writes to change control inputs (Writes to CMP_DACCR[DACEN], CMP_DACCR[VRSEL], CMP_DACCR[VOSEL], CMP_MUXCR[PSEL], and CMP_MUXCR[MSEL]) and the comparator output settling to a stable level.
3. 1 LSB = $V_{reference}$/64

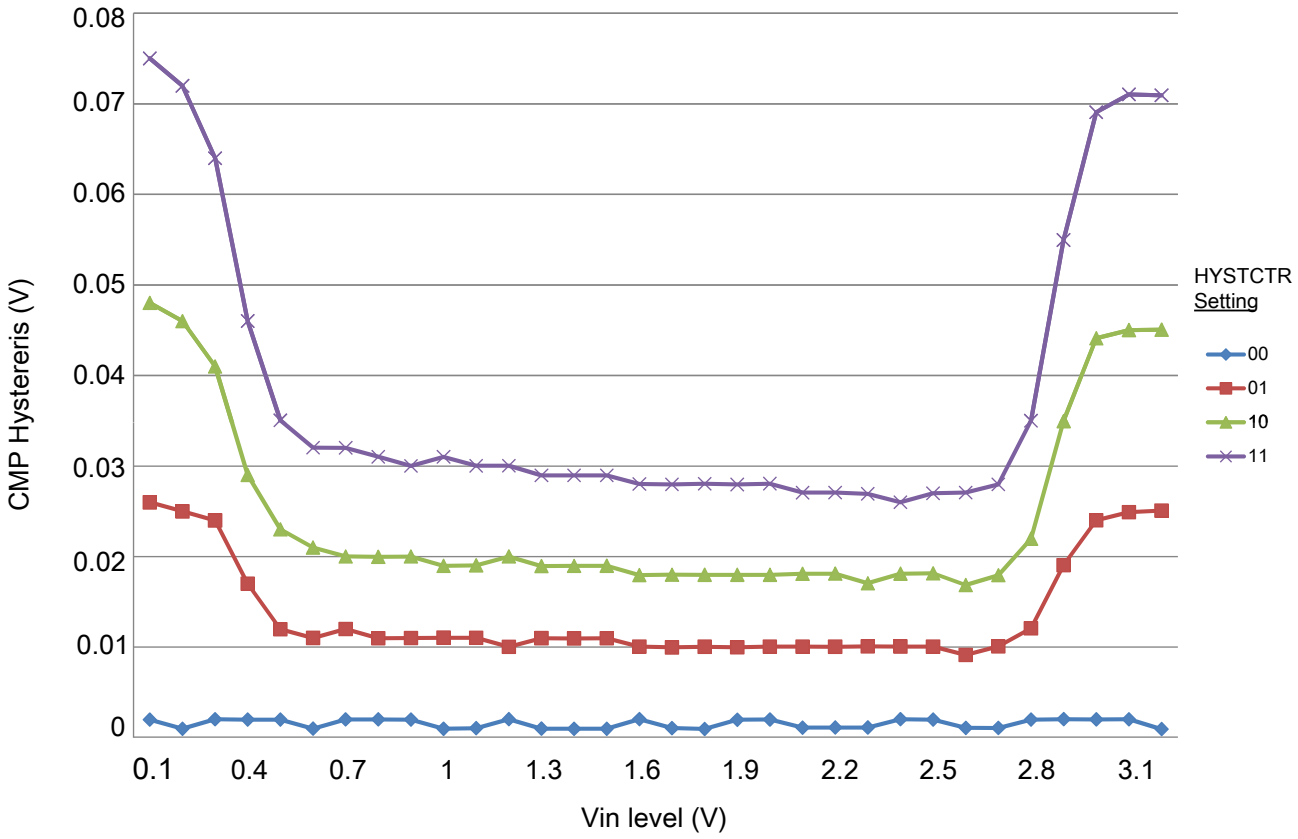


Figure 10. Typical hysteresis vs. Vin level (VDD = 3.3 V, PMODE = 0)

Table 33. VREF full-range operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{out}	Voltage reference output with factory trim at nominal V_{DDA} and temperature=25C	1.1915	1.195	1.1977	V	1
V_{out}	Voltage reference output — factory trim	1.1584	—	1.2376	V	1
V_{out}	Voltage reference output — user trim	1.193	—	1.197	V	1
V_{step}	Voltage reference trim step	—	0.5	—	mV	1
V_{tdrift}	Temperature drift (Vmax -Vmin across the full temperature range: 0 to 70°C)	—	—	50	mV	1
Ac	Aging coefficient	—	—	400	uV/yr	—
I_{bg}	Bandgap only current	—	—	80	µA	1
I_{lp}	Low-power buffer current	—	—	360	uA	1
I_{hp}	High-power buffer current	—	—	1	mA	1
ΔV_{LOAD}	Load regulation • current = ± 1.0 mA	—	200	—	µV	1, 2
T_{stup}	Buffer startup time	—	—	100	µs	—
V_{vdrift}	Voltage drift (Vmax -Vmin across the full voltage range)	—	2	—	mV	1

1. See the chip's Reference Manual for the appropriate settings of the VREF Status and Control register.
2. Load regulation voltage is the difference between the VREF_OUT voltage with no load vs. voltage with defined load

Table 34. VREF limited-range operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
T_A	Temperature	0	50	°C	—

Table 35. VREF limited-range operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
V_{out}	Voltage reference output with factory trim	1.173	1.225	V	—

3.7 Timers

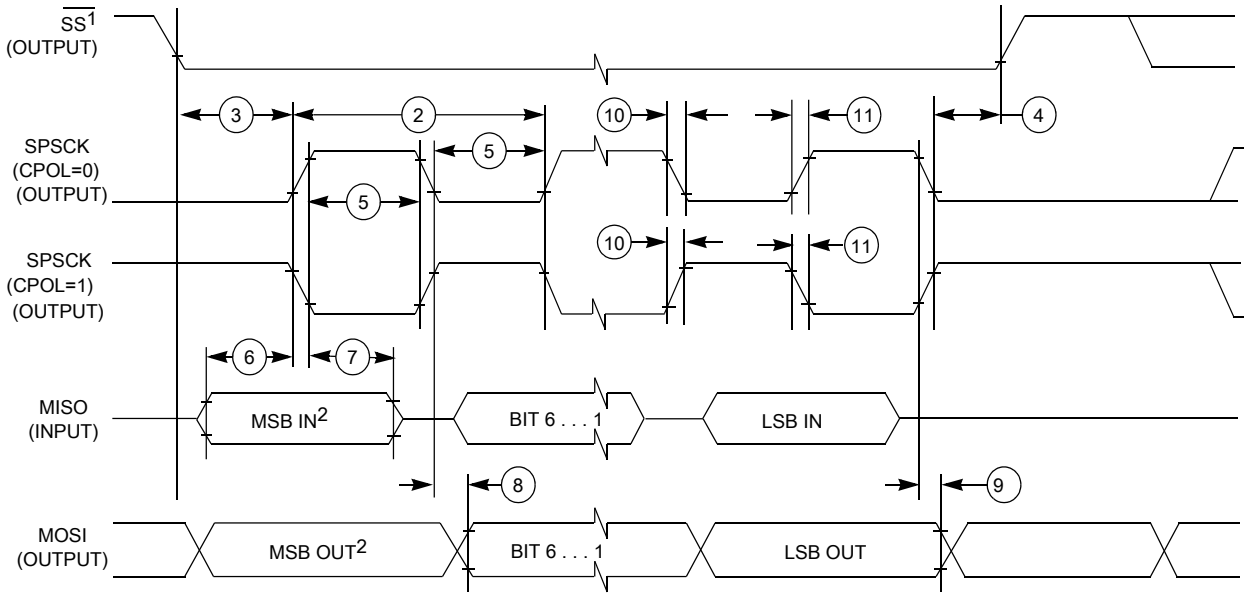
See General switching specifications.

3.8 Communication interfaces

Table 37. SPI master mode timing on slew rate enabled pads (continued)

Num.	Symbol	Description	Min.	Max.	Unit	Note
5	t_{WSPSCK}	Clock (SPSCK) high or low time	$t_{periph} - 30$	1024 x t_{periph}	ns	—
6	t_{SU}	Data setup time (inputs)	96	—	ns	—
7	t_{HI}	Data hold time (inputs)	0	—	ns	—
8	t_v	Data valid (after SPSCK edge)	—	52	ns	—
9	t_{HO}	Data hold time (outputs)	0	—	ns	—
10	t_{RI}	Rise time input	—	$t_{periph} - 25$	ns	—
	t_{FI}	Fall time input				
11	t_{RO}	Rise time output	—	36	ns	—
	t_{FO}	Fall time output				

1. For SPI0, f_{periph} is the bus clock (f_{BUS}).
2. $t_{periph} = 1/f_{periph}$



1. If configured as an output.
2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

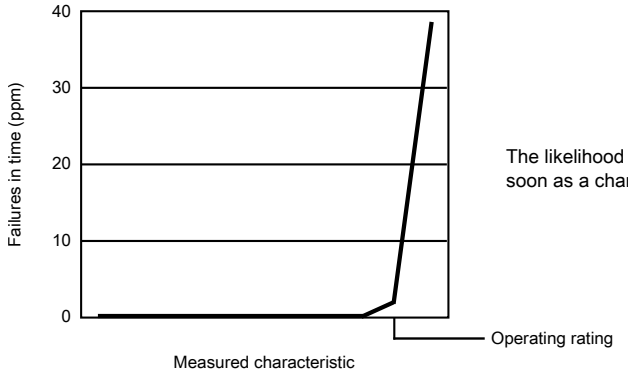
Figure 12. SPI master mode timing (CPHA = 0)

24 QFN	20 WLCSP	16 QFN	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5
17	A1	11	PTB3/ IRQ_10	DISABLED		PTB3/ IRQ_10	I2C0_SCL	LPUART0_TX		
18	B2	12	PTB4/ IRQ_11	DISABLED		PTB4/ IRQ_11	I2C0_SDA	LPUART0_RX		
19	A2	13	PTB5/ IRQ_12	NMI_b	ADC0_SE1/ CMP0_IN1	PTB5/ IRQ_12	TPM1_CH1	NMI_b		
20	B3	—	PTA12/ IRQ_13/ LPTMR0_ALT2	ADC0_SE0/ CMP0_IN0	ADC0_SE0/ CMP0_IN0	PTA12/ IRQ_13/ LPTMR0_ALT2	TPM1_CH0	TPM_CLKIN0		CLKOUT
21	A3	—	PTB13/ CLKOUT32K	DISABLED		PTB13/ CLKOUT32K	TPM1_CH1	RTC_CLKOUT		
22	A4	14	PTA0/ IRQ_0/ LLWU_P7	SWD_CLK	ADC0_SE15/ CMP0_IN2	PTA0/ IRQ_0/ LLWU_P7	TPM1_CH0	SWD_CLK		
23	B4	15	PTA1/ IRQ_1/ LPTMR0_ALT1	RESET_b		PTA1/ IRQ_1/ LPTMR0_ALT1	TPM_CLKIN0	RESET_b		
24	A5	16	PTA2	SWD_DIO		PTA2	CMP0_OUT	SWD_DIO		

5.2 KL03 pinouts

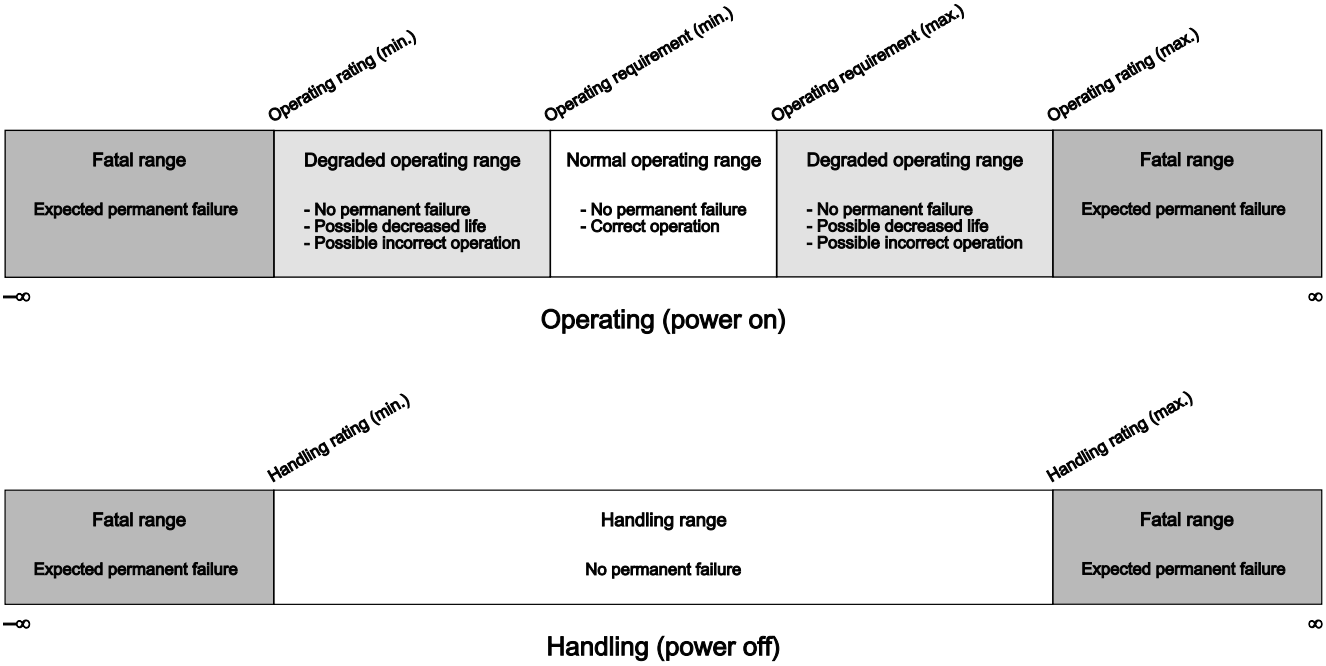
The following figures show the pinout diagrams for the devices supported by this document. Many signals may be multiplexed onto a single pin. To determine what signals can be used on which pin, see KL03 signal multiplexing and pin assignments.

8.5 Result of exceeding a rating



The likelihood of permanent chip failure increases rapidly as soon as a characteristic begins to exceed one of its operating ratings.

8.6 Relationship between ratings and operating requirements



8.7 Guidelines for ratings and operating requirements

Follow these guidelines for ratings and operating requirements:

- Never exceed any of the chip's ratings.

- During normal operation, don't exceed any of the chip's operating requirements.
- If you must exceed an operating requirement at times other than during normal operation (for example, during power sequencing), limit the duration as much as possible.

8.8 Definition: Typical value

A *typical value* is a specified value for a technical characteristic that:

- Lies within the range of values specified by the operating behavior
- Given the typical manufacturing process, is representative of that characteristic during operation when you meet the typical-value conditions or other specified conditions

Typical values are provided as design guidelines and are neither tested nor guaranteed.

8.8.1 Example 1

This is an example of an operating behavior that includes a typical value:

Symbol	Description	Min.	Typ.	Max.	Unit
I_{WP}	Digital I/O weak pullup/pulldown current	10	70	130	µA

8.8.2 Example 2

This is an example of a chart that shows typical values for various voltage and temperature conditions: